

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER/ STANDARD

PART NUMBER: TVR2G

MANUFACTURER: TOSHIBA

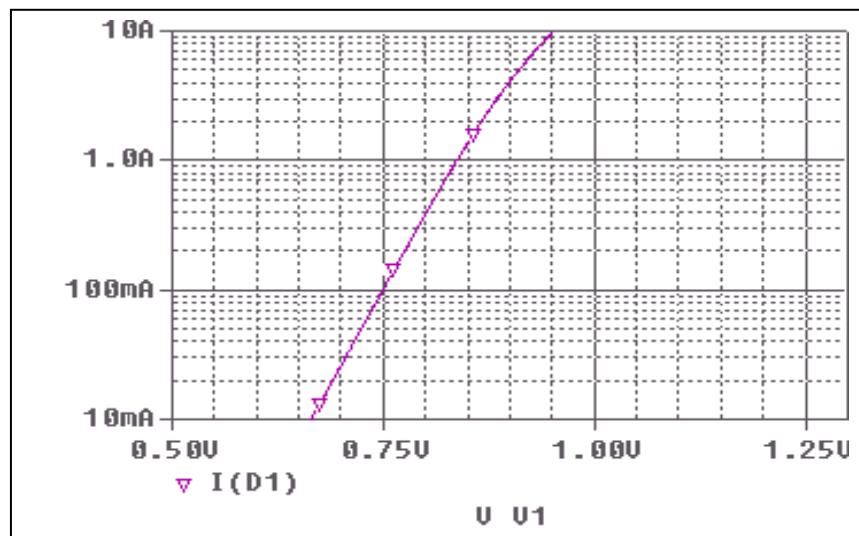


Bee Technologies Inc.

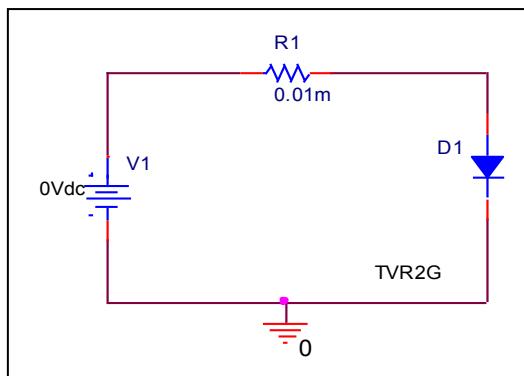
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

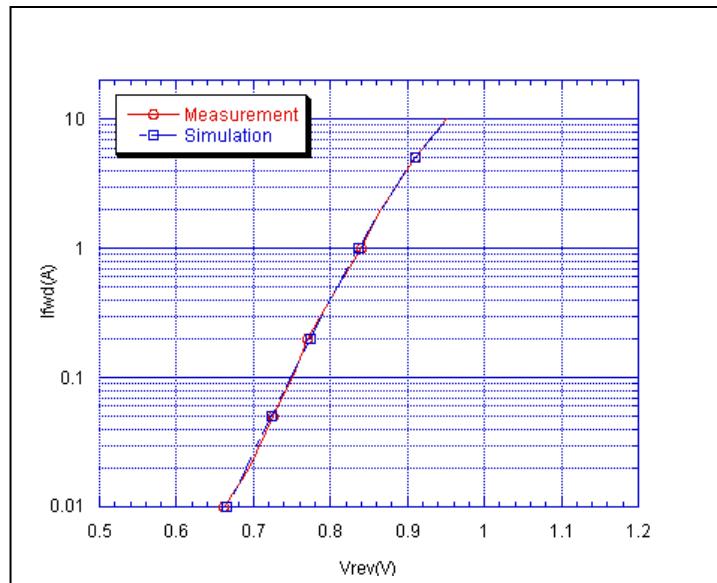


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

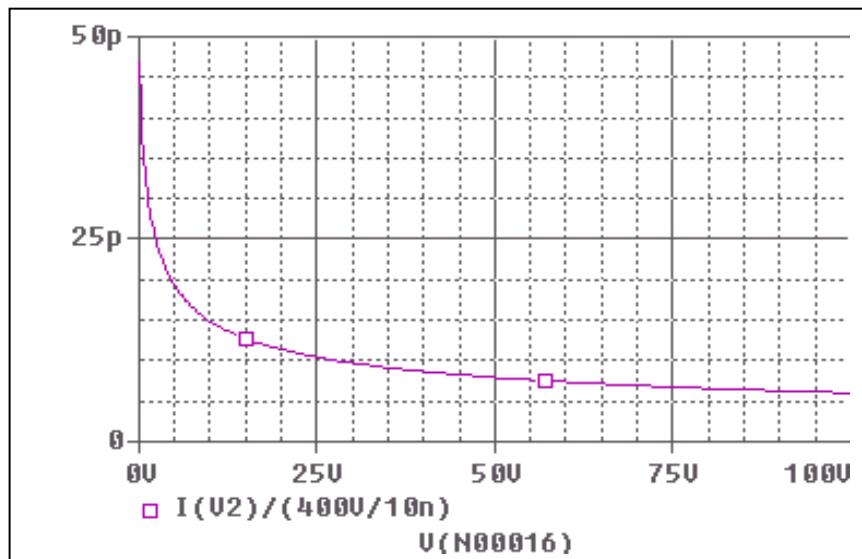


Simulation Result

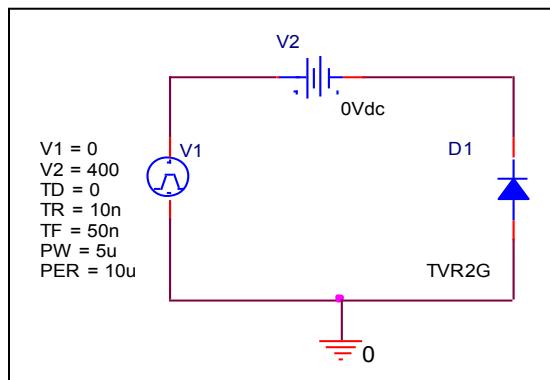
$I_{fwd}(A)$	$V_{fwd}(V)$ Measurement	$V_{fwd}(V)$ Simulation	%Error
0.01	0.662	0.665	-0.393
0.02	0.694	0.690	0.562
0.05	0.725	0.724	0.166
0.1	0.750	0.749	0.080
0.2	0.770	0.775	-0.675
0.5	0.810	0.810	0.012
1	0.840	0.837	0.310
2	0.866	0.866	-0.035
5	0.910	0.910	-0.033
10	0.952	0.952	0.000

Junction Capacitance Characteristic

Circuit Simulation Result

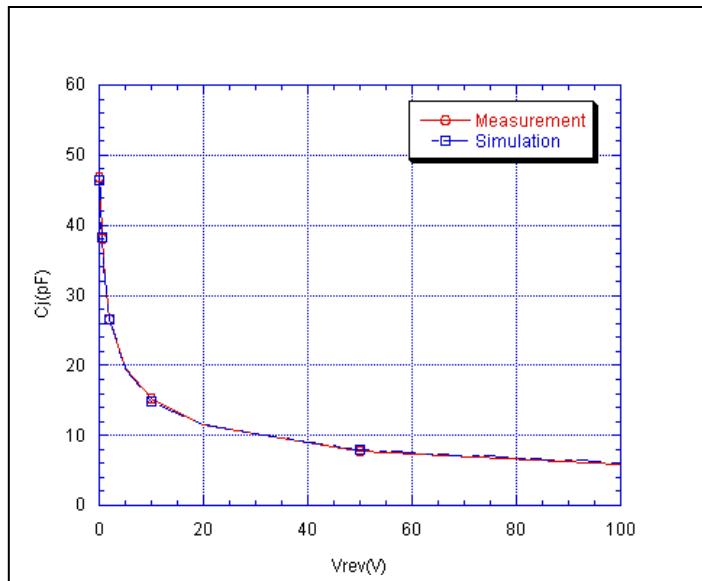


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

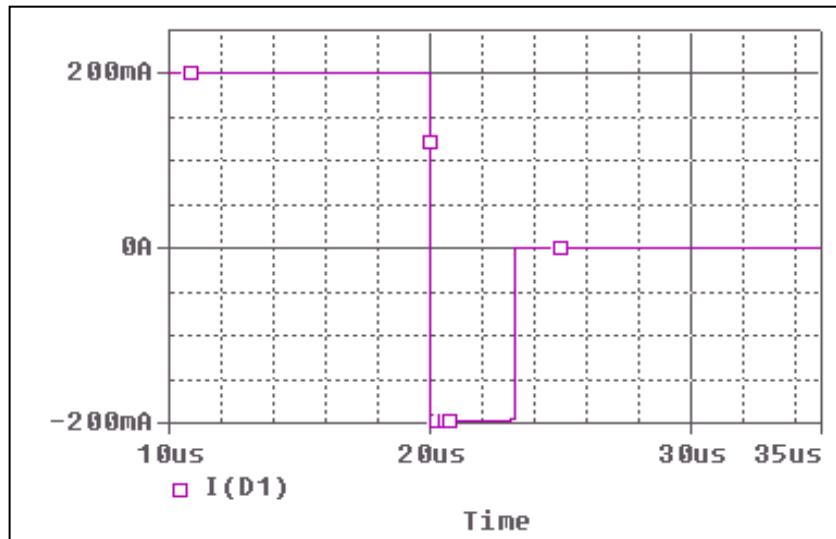


Simulation Result

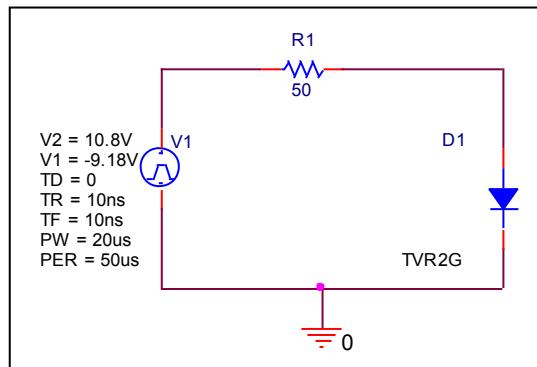
$V_{rev}(V)$	$C_j(pF)$ Measurement	$C_j(pF)$ Simulation	%Error
0	50.495	50.495	0.000
0.1	46.835	46.339	1.059
0.2	44.109	44.330	-0.501
0.5	38.096	38.170	-0.194
1	32.505	32.411	0.289
2	26.642	26.652	-0.038
5	19.664	19.371	1.490
10	15.185	14.953	1.528
20	11.482	11.415	0.584
50	7.723	7.941	-2.825
100	5.640	5.902	-4.637

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

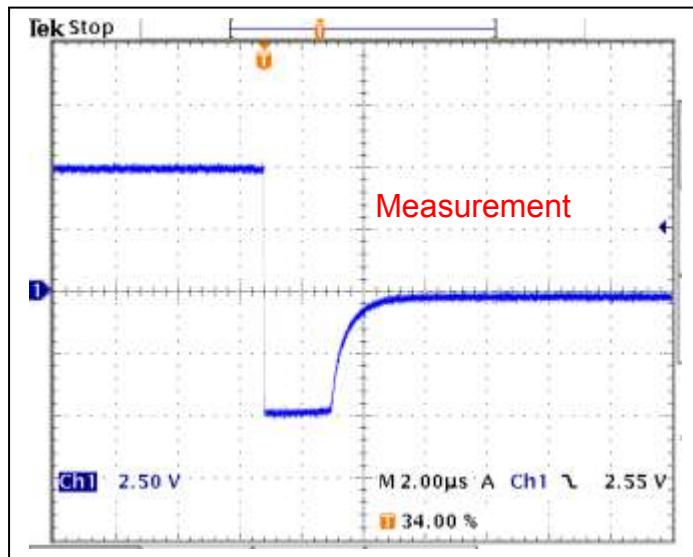


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	3.240	us	3.241	us	0.046

Reverse Recovery Characteristic

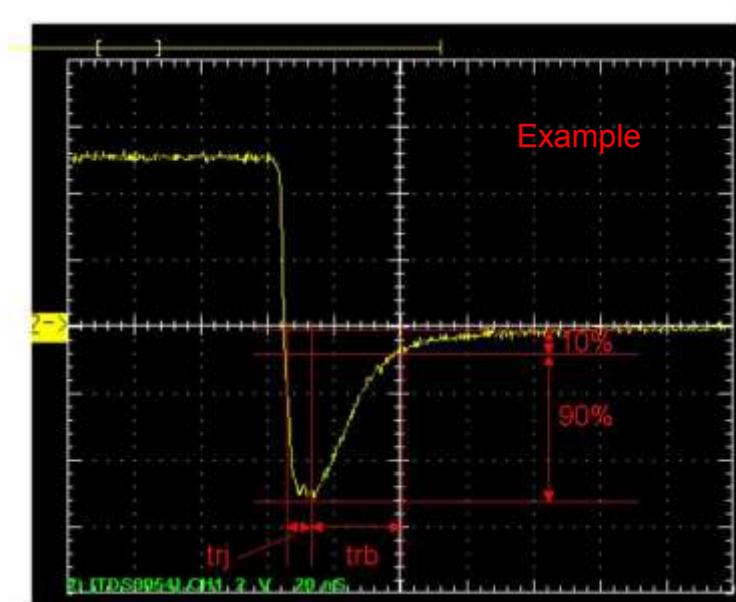
Reference



$Trj = 2.04(\mu s)$

$Trb = 1.20(\mu s)$

Conditions: $I_{fwd} = I_{rev} = 0.2(A)$, $R_L = 50$



Relation between trj and trb